

Form PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DKT. NO. 501.37436VC2	APPLICATION NO. TBD
INFORMATION DISCLOSURE STATEMENT BY APPLICANT  (Use several sheets if necessary)		APPLICANT Nishihara, et al.	
		FILING DATE November 26, 2003	EXPECTED GROUP 2811

## U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date
<i>JH</i>	AA 5,691,225	11/25/1997	Abiko			
<i>JH</i>	AB 5,652,176	7/29/1997	Maniar, et al.			
<i>JH</i>	AC 5,736,461	4/7/1998	Berti, et al.			
<i>JH</i>	AD 5,316,977	5/31/1994	Kunishima, et al.			
<i>JH</i>	AE 5,576,579	11/19/1996	Agnello, et al.			

## FOREIGN PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
<i>JH</i>	AE						
<i>JH</i>	AF						
<i>JH</i>	AG						

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>JH</i>	AH	Chinese Office Action dated December 27, 2002, for corresponding Application No. 97182025.2 with English Translation
<i>JH</i>	AI	Patent Abstracts of Japan, for Publication No. 07003486A, published January 6, 1995
Examiner <i>Yvonne A. Hurley</i>		Date Considered 5/11/04

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup>Applicant's unique citation designation number (optional). <sup>2</sup>See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup>Enter Office that issued the document, by the two-letter code (WIPO Standard St.3). <sup>4</sup>For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup>Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC.

**FORM PTO-1449** U.S. Department of Commerce  
(Rev. 4/92) Patent and Trademark Office

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

(Use several sheets if necessary)

ATTY. DOCKET NO.

501.37436CV2

APPLICATION NO.

TBD

APPLICANT

S. NISHIHARA, et al.

FILING DATE

November 26, 2003

EXPECTED GROUP

2811

**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
JH	5,998,284	12/07/1999	Azuma			
JH	6,018,185	01/25/2000	Mitani, et al.			
JH	6,124,189	09/26/2000	Watanabe, et al.			

**FOREIGN PATENT DOCUMENTS**

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation/ ABSTRACT	
						YES	NO
JH	6-192874	07/12/1994	Japan			X	
JH	6-192879	07/12/1994	Japan			X	
JH	6-204420	07/22/1994	Japan			X	
JH	7-78788	3/20/1995	Japan			X	
JH	8-167661	6/25/1996	Japan				X
JH	8-279509	10/22/1996	Japan				X
JH	9-69497	03/11/1997	Japan				X
JH	9-82810	03/28/1997	Japan			X	

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

JH	W.T. Lynch, et al., Self-Aligned Contact Schemes For Source-Drains In Submicron Devices, 1987, pps. 354-357, IEEE
JH	Shyam P. Muraka, Self-aligned silicides or metals for very large scale integrated circuit applications, Nov/Dec 1986, pps. 1325-1331, J. Vac. Sci. Technol. B 4 (6)
JH	Eiji Nagasawa, et al., Mo- and Ti-Silicided Low-Resistance Shallow Junctions Formed Using th Ion Implantation Through Metal Technique, March 1987, IEEE Transactions On Electron Devices, Vol. Ed-34, No. 3

EXAMINER

*Yvonne A. Hurley*

DATE CONSIDERED

5/11/04

EXAMINER: Initial if citation is considered, draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

**FORM PTO-1449** U.S. Department of Commerce  
(Rev. 4/92) Patent and Trademark Office

ATTY. DOCKET NO.

APPLICATION NO.

501.37436CV2

TBD

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

(Use several sheets if necessary)

APPLICANT

S. NISHIHARA, et al.

FILING DATE

November 26, 2003

EXPECTED GROUP

2811

**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>GH</i>	4,821,085	4/11/1989	Haken, et al.			
<i>HH</i>	5,635,426	6/3/1997	Hayashi, et al.			
<i>HH</i>	5,742,090	4/4/1996	Stolmeijer, et al.			
<i>HH</i>	5,780,362	7/14/1998	Wang, et al.			

**FOREIGN PATENT DOCUMENTS**

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation/ ABSTRACT	
						YES	NO
<i>HH</i>	9-293790	11/11/1997	Japan			X	
<i>HH</i>	9-312391	12/02/1997	Japan				X
<i>HH</i>	9-320990	12/12/1997	Japan				X
<i>HH</i>	10-74846	03/17/1998	Japan				X
<i>HH</i>	10-163485	06/19/1998	Japan			X	
<i>HH</i>	10-294462	11/04/1998	Japan				X
<i>HH</i>	7-3486	01/6/1995	Japan				X

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

<i>HH</i>	J.M. Poate, Silicide Formation, Thin Films - Interdiffusion and Reactions, pps. 359-405
<i>HH</i>	Thomas E. Tang, et al., Titanium Nitride Local Interconnect Technology for VLSI, March 1987, pps. 682-688, Electron Devices, Vol. Ed-34, No. 3
<i>HH</i>	R.D.J. Verhaar, et al., Self-aligned CoSi <sub>2</sub> in a Submicron CMOS Process, pps. 229-232
<i>HH</i>	Takao, et al., "A 4-um <sup>2</sup> Full-CMOS SRAM Cell Technology for 0.2-um High-Performance Logic LSIs", 1997 Symposium on VLSI Technology Digest of Technical Papers, pages 11 and 12

EXAMINER

*Yuan D. Hu*

DATE CONSIDERED

5/11/04

EXAMINER: Initial if citation is considered, draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449 U.S. Department of Commerce  
(Rev. 4/92) Patent and Trademark Office

INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT

(Use several sheets if necessary)

ATTY. DOCKET NO.

501.37436CV2

APPLICATION NO.

TBD

APPLICANT

S. NISHIHARA, et al.

FILING DATE

November 26, 2003

EXPECTED GROUP

2811

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
JH	5,047,367	09/10/1991	Wei, et al.			
JH	5,268,590	12/7/1993	Priester, et al.			
JH	5,316,977	05/31/1994	Kunishima, et al.			
JH	5,635,426	06/03/1997	Hayashi, et al.			
JH	5,721,175	02/24/1998	Kunishima, et al.			
JH	5,780,361	07/14/1998	Inoue			
JH	5,843,841	12/01/1998	Izawa, et al.			
JH	5,850,096	12/15/1998	Izawa, et al.			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation/ ABSTRACT	
						YES	NO
JH	5-90293	04/09/1993	Japan			X	
JH	5-182982	7/23/1993	Japan				X
JH	5-102078	4/23/1993	Japan				X
JH	5-343632	12/24/1993	Japan				X
JH	6-192874	7/12/1994	Japan			X	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

JH	D.L. Kwong, et al., silicided shallow junction formation by ion implantation of impurity ions into silicide layers and subsequent drive-in, 1 June 1997, pps. 5084-5088, J. Appl. Phys. 61 (11)
JH	R. Liu, et al., Formation of Shallow p <sup>+</sup> /n AND n <sup>+</sup> /p Junctions with CoSi <sub>2</sub> , pps. 446-462
JH	Chih-Yuan Lu, et al., A Folded Extended Window MOSFET for ULSI Applications, August 1988, pps. 388-390, IEEE Electron Device Letters, Vol. 9, No. 8

EXAMINER

*James A. Hurley*

DATE CONSIDERED

5/11/04

EXAMINER: Initial if citation is considered, draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.